



**THE DATASHEET OF
STH180N10F3-6**



N-channel 100 V, 3.9 mΩ typ., 180 A, STripFET™ F3 Power MOSFET in H²PAK-6 package

Datasheet - production data

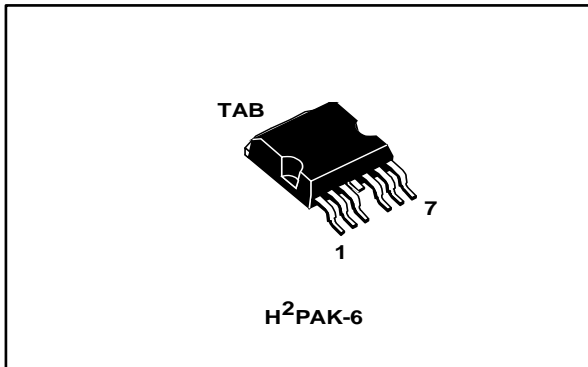
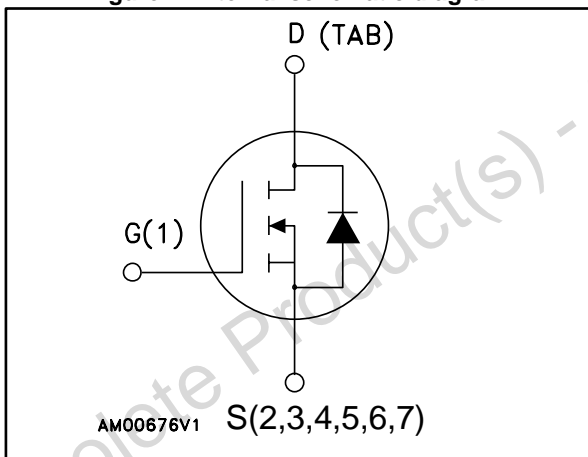


Figure 1: Internal schematic diagram



Features

Order code	V _{DS}	R _{DS(on)} max.	I _D
STH180N10F3-6	100 V	4.5 mΩ	180 A

- Low on-resistance R_{DS(on)}
- 100% avalanche tested

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using STripFET™ F3 technology. It is designed to minimize on-resistance and gate charge to provide superior switching performance.

Table 1: Device summary

Order code	Marking	Package	Packing
STH180N10F3-6	180N10F3	H ² PAK-6	Tape and reel

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Obsolete Product(s) - Obsolete Product(s)

1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	100	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	180	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	120	A
$I_{DM}^{(2)}$	Drain current (pulsed)	720	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	315	W
	Derating factor	2.1	W/ $^\circ\text{C}$
dv/dt	Peak diode recovery voltage slope	20	V/ns
$E_{AS}^{(3)}$	Single pulse avalanche energy	350	mJ
T_J	Operating junction temperature	-55 to 175	$^\circ\text{C}$
T_{stg}	Storage temperature		$^\circ\text{C}$

Notes:

- (1) Current limited by package
- (2) Pulse width limited by safe operating area
- (3) Starting $T_J = 25\text{ }^\circ\text{C}$, $I_D = 80$, $V_{DD} = 50\text{ V}$

Table 3: Thermal resistance

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	0.48	$^\circ\text{C/W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	35	$^\circ\text{C/W}$

Notes:

- (1) When mounted on FR-4 board of 1 inch², 2 oz Cu

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified)

Table 4: On/off-state

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage ($V_{GS} = 0$)	$I_D = 250\ \mu A$	100			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 100\ V$			10	μA
		$V_{DS} = 100\ V$; $T_C = 125\text{ °C}$			100	μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\ V$			± 200	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\ \mu A$	2		4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\ V$, $I_D = 60\ A$		3.9	4.5	m Ω

Table 5: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit	
C_{iss}	Input capacitance	$V_{DS} = 25\ V$, $f = 1\ MHz$, $V_{GS} = 0$	-	6665	-	pF	
C_{oss}	Output capacitance			786		pF	
C_{rss}	Reverse transfer capacitance			49		pF	
Q_g	Total gate charge			$V_{DD} = 50\ V$, $I_D = 120\ A$		114.6	nC
Q_{gs}	Gate-source charge			$V_{GS} = 10\ V$		38.8	nC
Q_{gd}	Gate-drain charge			See Figure 14: "Gate charge test circuit"		31.9	nC

Table 6: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 50\ V$, $I_D = 60\ A$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\ V$ See Figure 13: "Switching times test circuit for resistive load"	-	25.6	-	ns
t_r	Rise time			97.1		ns
$t_{d(off)}$	Turn-off delay time			99.9		ns
t_f	Fall time			6.9		ns

Table 7: Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit	
I_{SD}	Source-drain current		-		180	A	
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				720	A	
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 120 \text{ A}, V_{GS} = 0$				1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 120 \text{ A},$ $di/dt = 100 \text{ A}/\mu\text{s},$			83.4		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 80 \text{ V}, T_j = 150$ $^{\circ}\text{C}$			295.7		nC
I_{RRM}	Reverse recovery current				7.1		A

Notes:

⁽¹⁾Pulse width limited by safe operating area

⁽²⁾Pulsed: pulse duration = 300 μs , duty cycle 1.5%

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2.1 Electrical characteristics (curves)

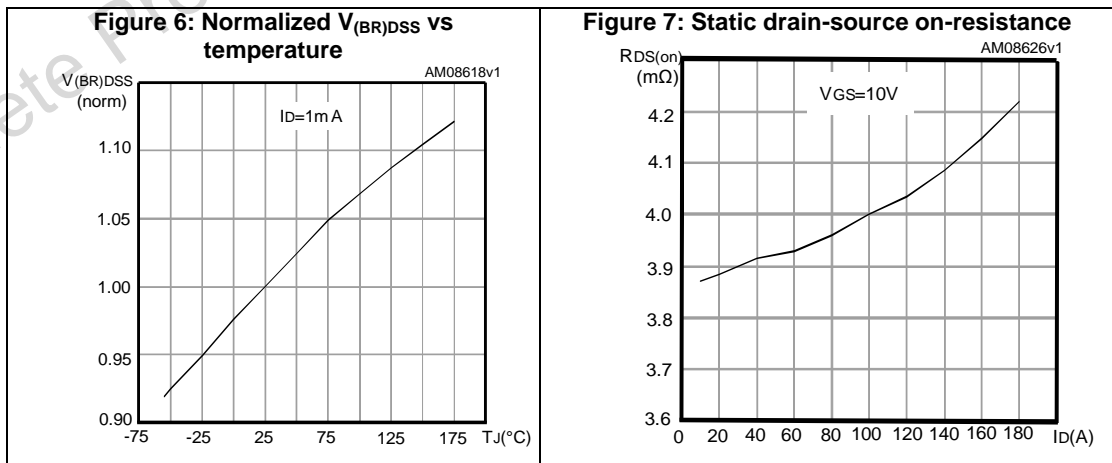
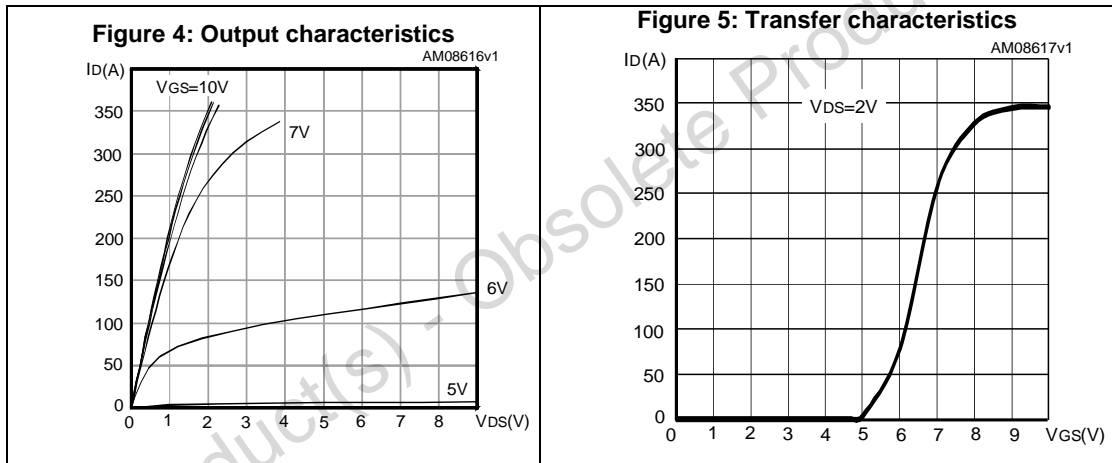
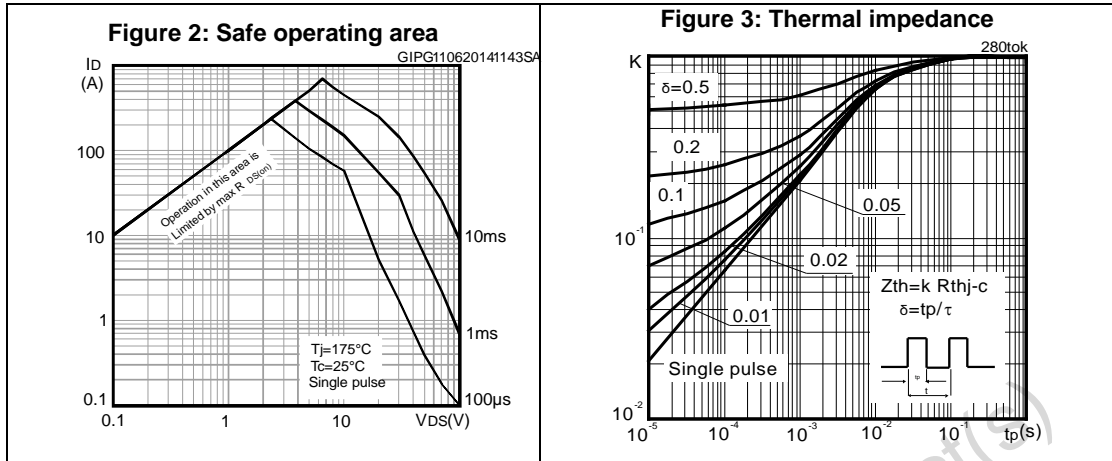


Figure 8: Gate charge vs gate-source voltage

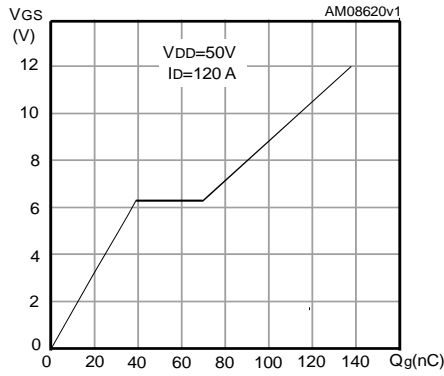


Figure 9: Capacitance variations

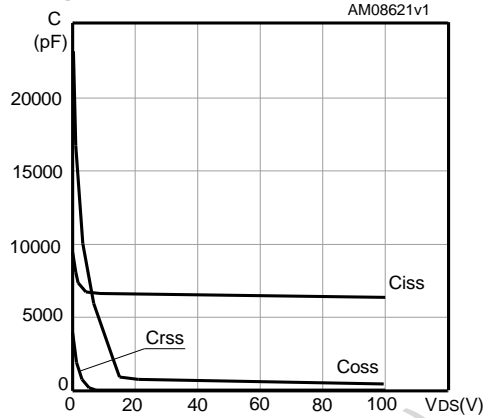


Figure 10: Normalized gate threshold voltage vs temperature

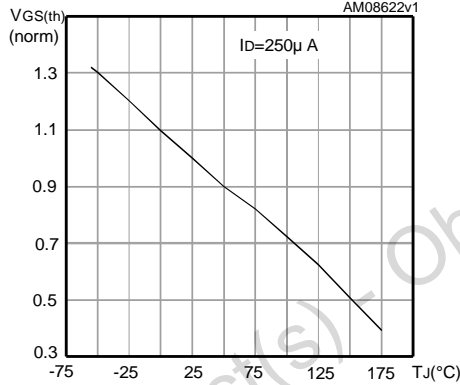


Figure 11: Normalized on-resistance vs temperature

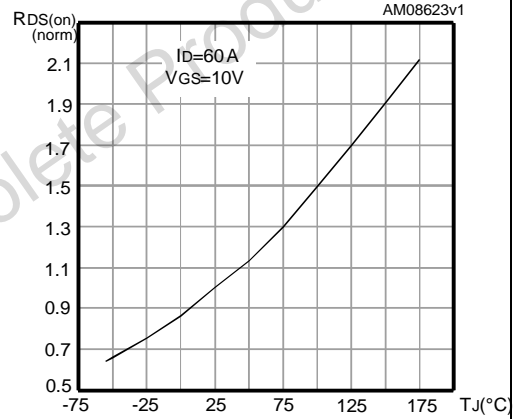
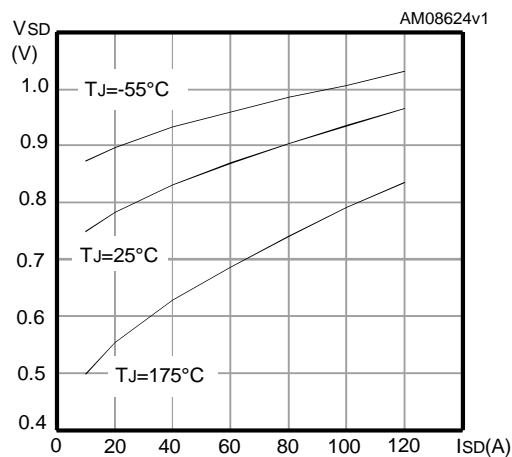
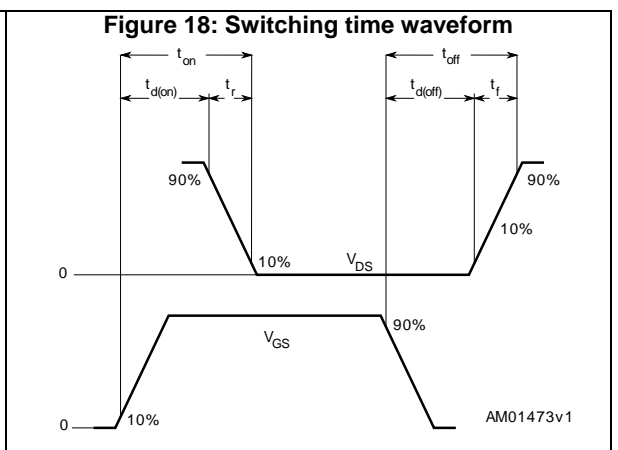
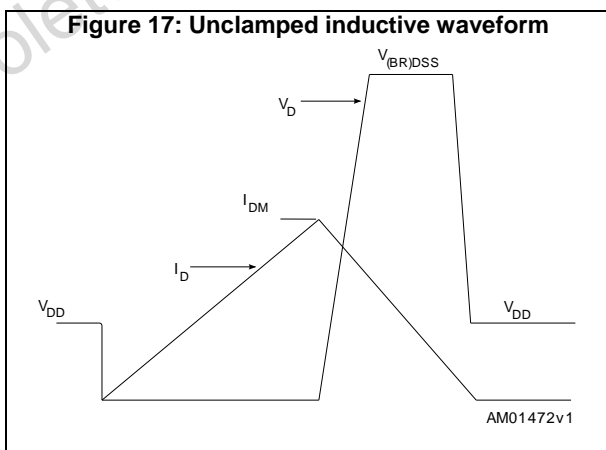
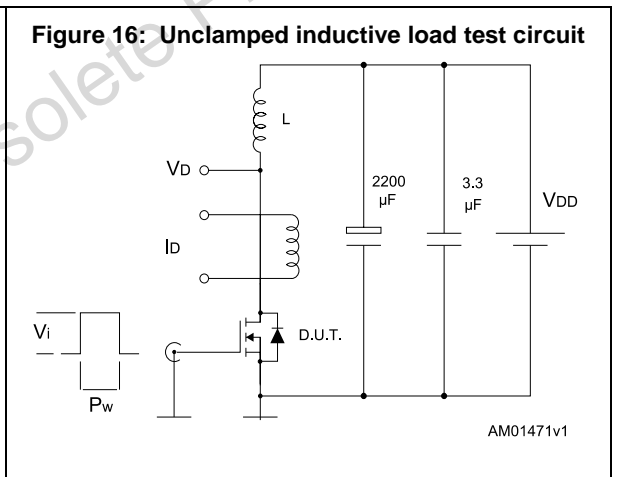
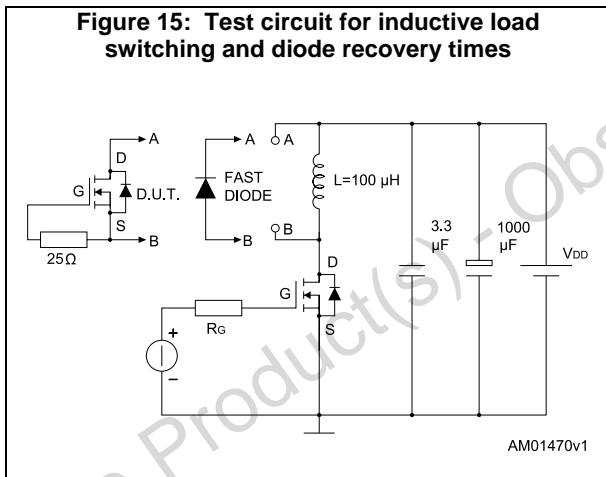
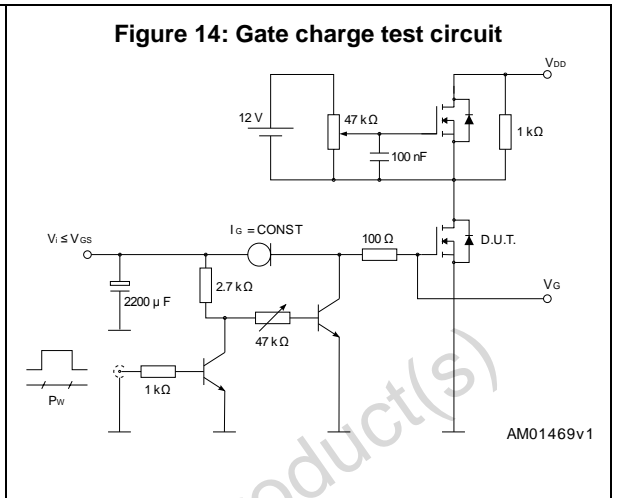
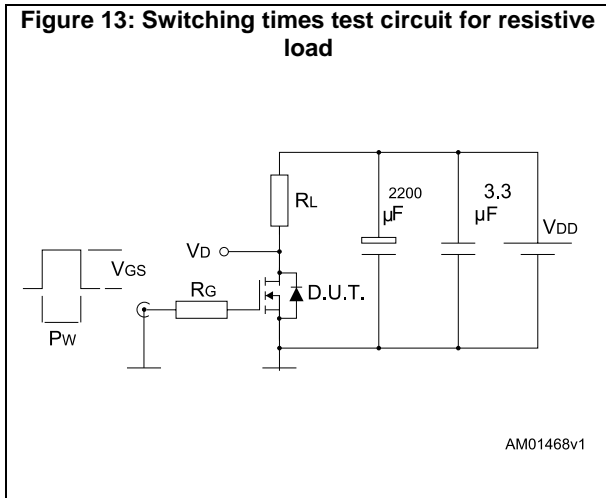


Figure 12: Source-drain diode forward characteristics



3 Test circuits



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 H²PAK-6 package information

Figure 19: H²PAK-6 outline

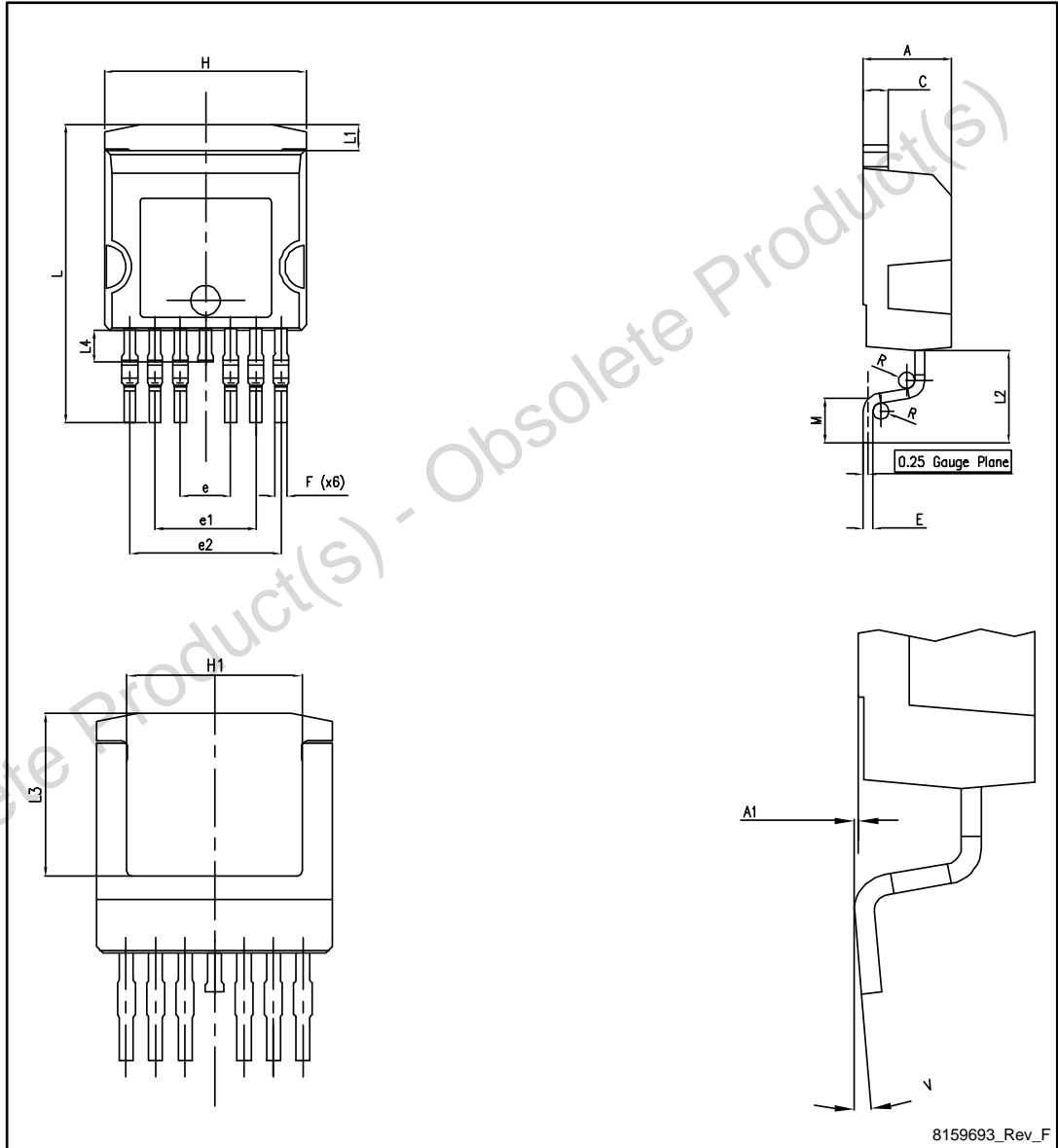
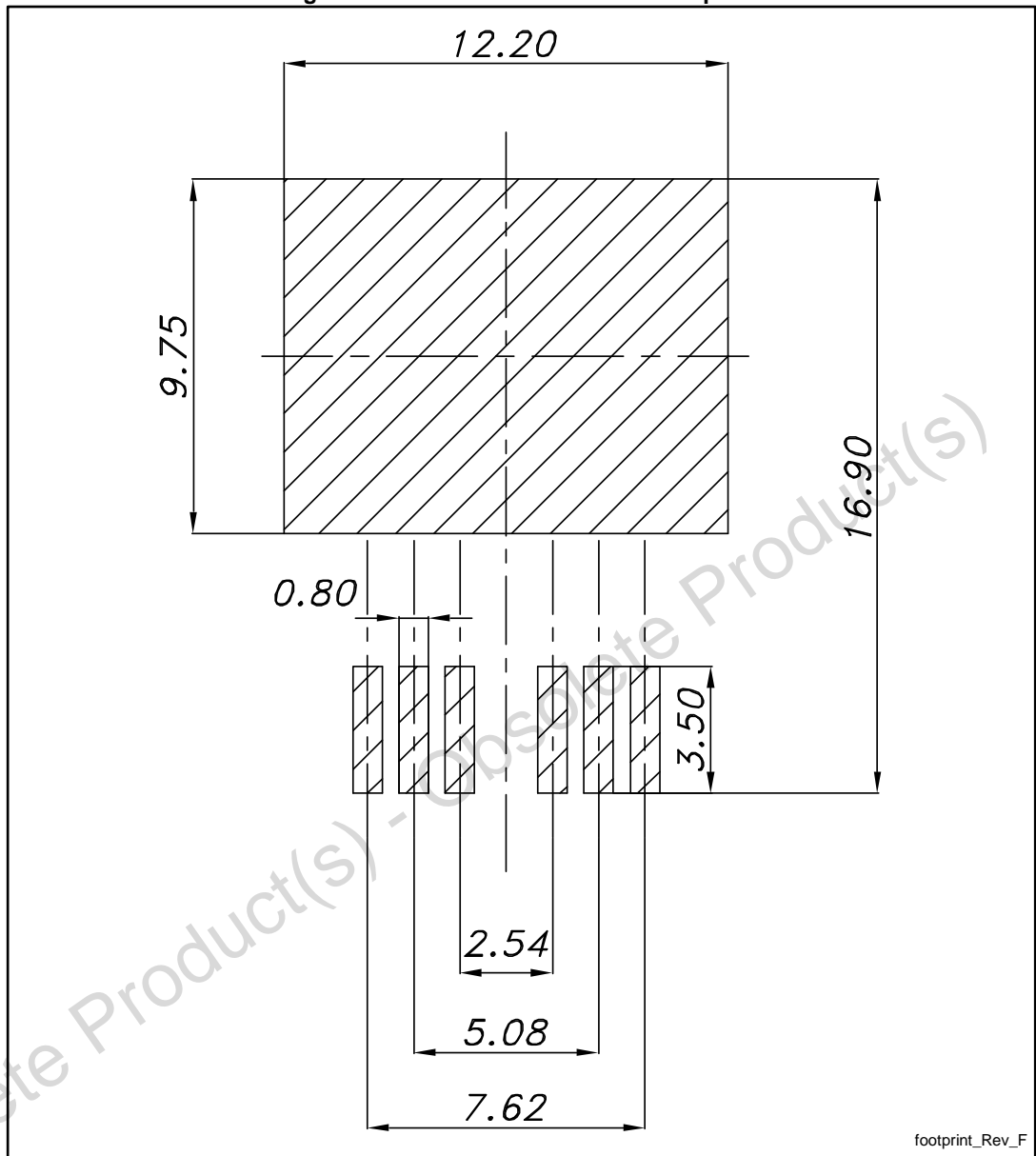


Table 8: H²PAK-6 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.30		4.80
A1	0.03		0.20
C	1.17		1.37
e	2.34		2.74
e1	4.88		5.28
e2	7.42		7.82
E	0.45		0.60
F	0.50		0.70
H	10.00		10.40
H1	7.40		7.80
L	14.75		15.25
L1	1.27		1.40
L2	4.35		4.95
L3	6.85		7.25
L4	1.5		1.75
M	1.90		2.50
R	0.20		0.60
V	0°		8°

Figure 20: H²PAK-6 recommended footprint



Dimensions are in mm.

4.2 Packing information

Figure 21: Tape outline

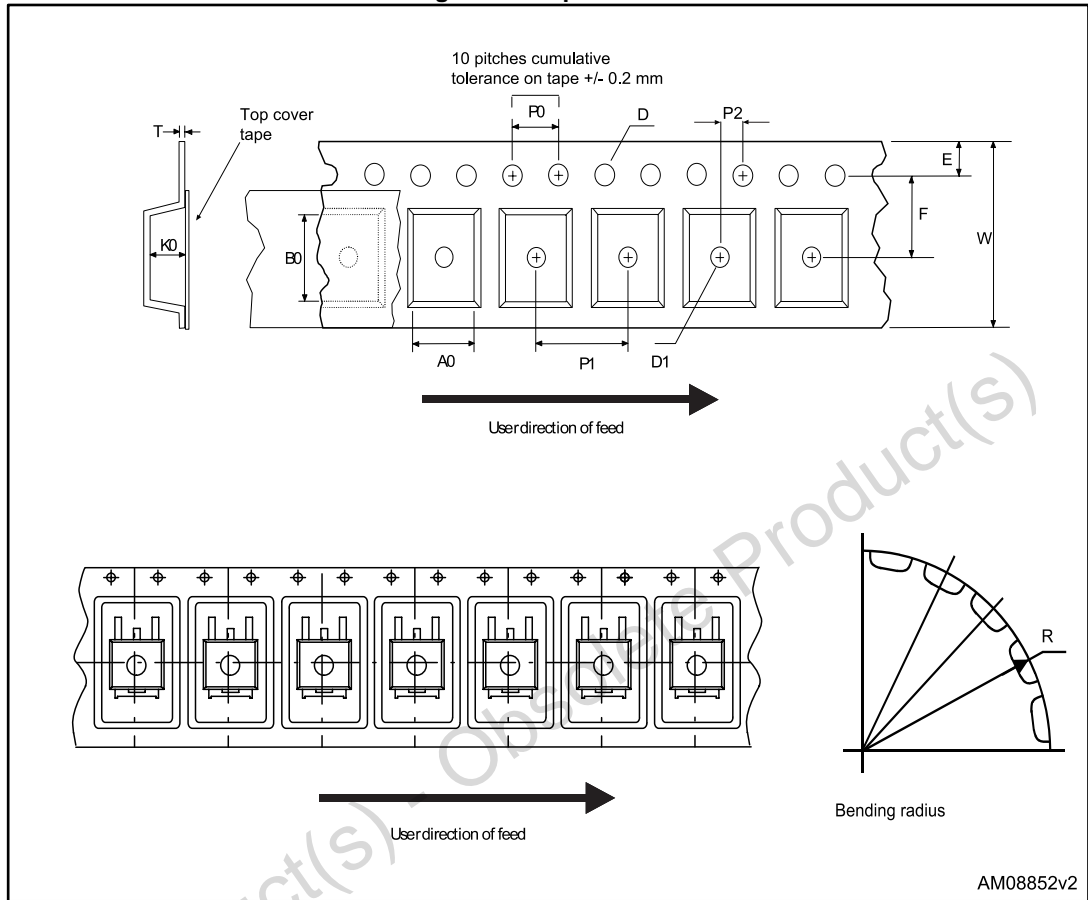


Figure 22: Reel outline

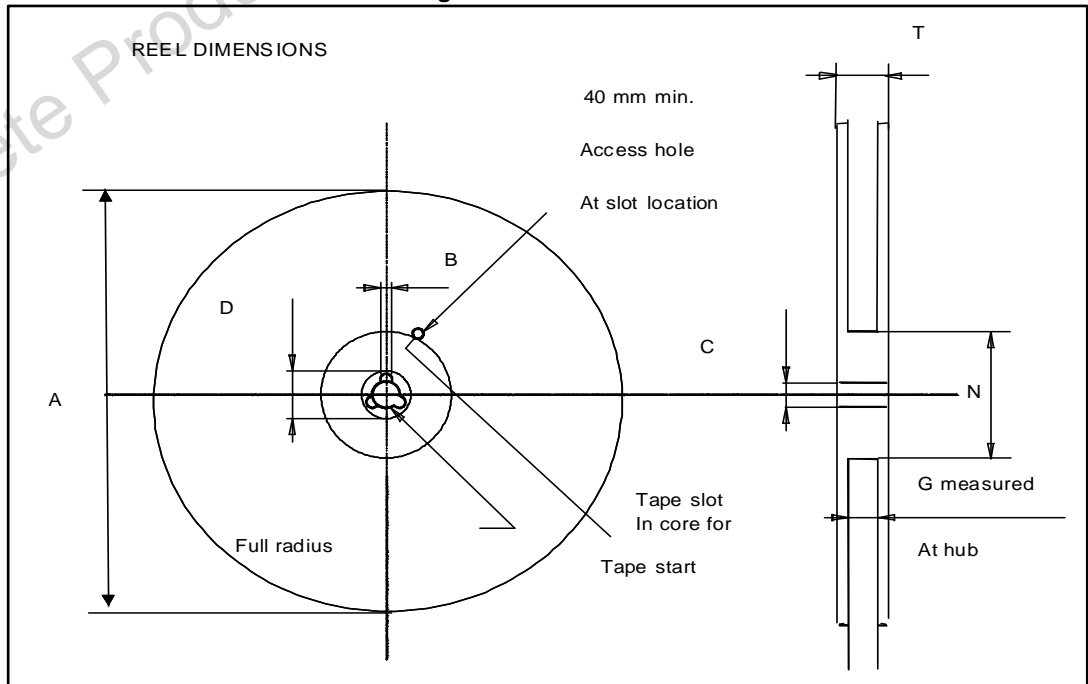


Table 9: Tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base quantity		1000
P2	1.9	2.1	Bulk quantity		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

Obsolete Product(s) - Obsolete Product(s)

5 Revision history

Table 10: Document revision history

Date	Revision	Changes
10-Oct-2011	1	First version
04-Nov-2011	2	<ul style="list-style-type: none">Updated features in cover page
14-Nov-2014	3	<ul style="list-style-type: none">Updated: H²PAK-6 package mechanical data.Updated: title, features and description.Minor text changes.
26-Nov-2014	4	Updated Table 4: "On/off-state" .

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